

# High-speed double diode Rev. 3 — 22 July 2010

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Two high-speed switching diodes fabricated in planar technology, and encapsulated in a small SOT143B Surface-Mounted Device (SMD) plastic package. The diodes are not connected.

#### 1.2 Features and benefits

■ High switching speed:  $t_{rr} \le 4$  ns

Reverse voltage: V<sub>R</sub> ≤ 75 V

Repetitive peak reverse voltage: V<sub>RRM</sub> ≤ 85 V Repetitive peak forward current: I<sub>FRM</sub> ≤ 500 mA

AEC-Q101 qualified

Small SMD package

### 1.3 Applications

High-speed switching in e.g. surface-mounted circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I <sub>F</sub>	forward current		<u>[1]</u> _	-	215	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 75 V	-	-	1	μΑ
$V_R$	reverse voltage		-	-	75	V
t <sub>rr</sub>	reverse recovery time		[2] _	-	4	ns

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB).

[2] When switched from  $I_F$  = 10 mA to  $I_R$  = 10 mA;  $R_L$  = 100  $\Omega$ ; measured at  $I_R$  = 1 mA.



### **High-speed double diode**

### 2. Pinning information

Table 2. Pinning

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode (diode 1)		
2	cathode (diode 2)	4 3	4 3
3	anode (diode 2)		
4	anode (diode 1)	1 2	
			1 2
			006aab100

## 3. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
BAS28	-	plastic surface-mounted package; 4 leads	SOT143B			

### 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
BAS28	JT*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

### High-speed double diode

## 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		-	85	V
V <sub>R</sub>	reverse voltage		-	75	V
l <sub>F</sub>	forward current		<u>[1]</u> -	215	mA
I <sub>FRM</sub>	repetitive peak forward current		-	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave	<u>[3]</u>		
		t <sub>p</sub> = 1 μs	-	4	Α
		$t_p = 1 \text{ ms}$	-	1	Α
		t <sub>p</sub> = 1 s	-	0.5	Α
Per device	)				
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1][2]	250	mW
Tj	junction temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB.

### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per device;	one diode loaded					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
$R_{th(j-t)}$	thermal resistance from junction to tie-point		-	-	360	K/W

<sup>[1]</sup> Device mounted on an FR4 PCB.

<sup>[2]</sup> One diode loaded.

<sup>[3]</sup>  $T_j = 25$  °C prior to surge.

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### 7. Characteristics

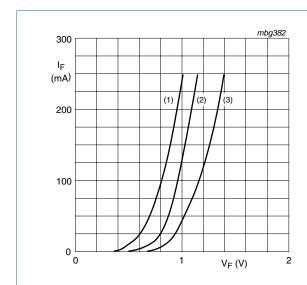
Table 7. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	•					
V <sub>F</sub> forward voltage	I <sub>F</sub> = 1 mA	-	-	715	mV	
	I <sub>F</sub> = 10 mA	-	-	855	mV	
	I <sub>F</sub> = 50 mA	-	-	1	V	
	I <sub>F</sub> = 150 mA	-	-	1.25	V	
I <sub>R</sub> reverse current	reverse current	V <sub>R</sub> = 25 V	-	-	30	nΑ
		V <sub>R</sub> = 75 V	-	-	1	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	-	-	30	μΑ
		V <sub>R</sub> = 75 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
$C_d$	diode capacitance	$f = 1 MHz; V_R = 0 V$	-	-	1.5	pF
t <sub>rr</sub>	reverse recovery time		<u>[1]</u> -	-	4	ns
$V_{FR}$	forward recovery voltage		[2] _	-	1.75	V

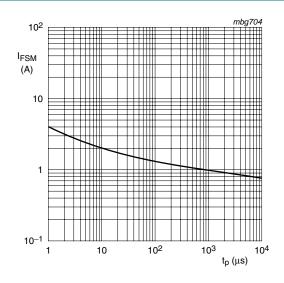
<sup>[1]</sup> When switched from  $I_F = 10$  mA to  $I_R = 10$  mA;  $R_L = 100$   $\Omega$ ; measured at  $I_R = 1$  mA.

<sup>[2]</sup> When switched from  $I_F = 10$  mA;  $t_r = 20$  ns.



- (1)  $T_j = 150 \,^{\circ}\text{C}$ ; typical values
- (2)  $T_j = 25$  °C; typical values
- (3)  $T_j = 25 \,^{\circ}C$ ; maximum values

Fig 1. Forward current as a function of forward voltage

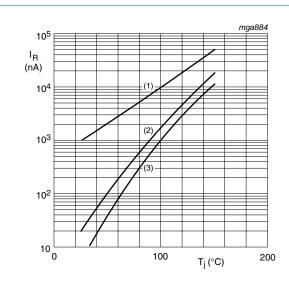


Based on square wave currents.

 $T_j = 25$  °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values

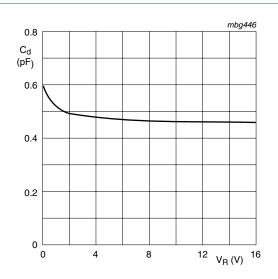
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 $V_R = V_{Rmax}$ 

- (1)  $V_R = 75 \text{ V}$ ; maximum values
- (2)  $V_R = 75 \text{ V}$ ; typical values
- (3)  $V_R = 25 \text{ V}$ ; typical values

Fig 3. Reverse current as a function of junction temperature



 $f = 1 \text{ MHz}; T_j = 25 ^{\circ}\text{C}$ 

Fig 4. Diode capacitance as a function of reverse voltage; typical values

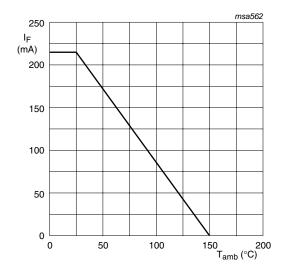
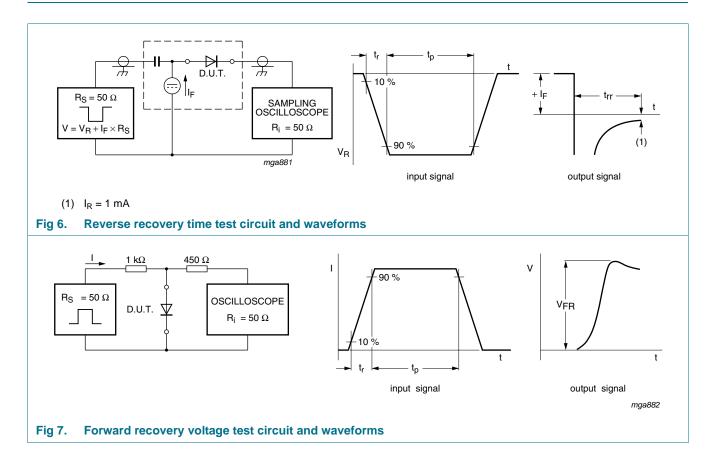


Fig 5. Forward current as a function of ambient temperature; derating curve

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### 8. Test information

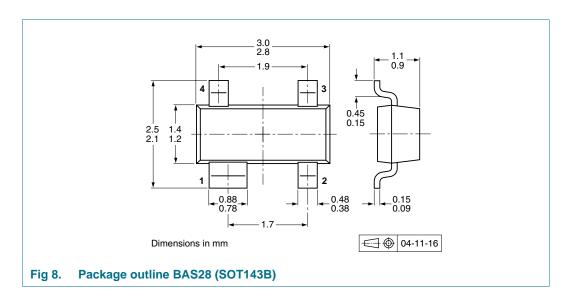


### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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### 9. Package outline



## 10. Packing information

Table 8. Packing methods

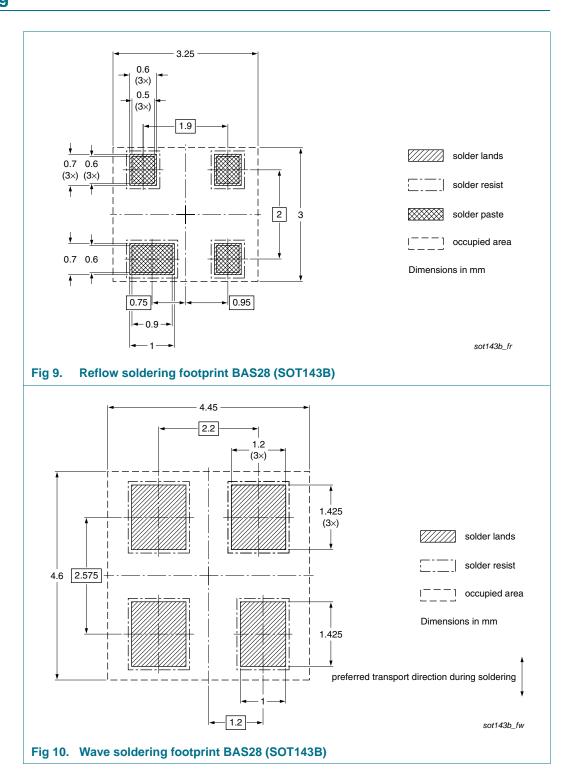
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BAS28	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

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### 11. Soldering



### High-speed double diode

## 12. Revision history

### Table 9. Revision history

	•						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAS28 v.3	20100722	Product data sheet	-	BAS28_2			
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity			
	<ul> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>						
	<ul> <li>Section 1.1</li> </ul>	"General description": ame	ended				
	<ul> <li>Section 4 "Marking": updated</li> </ul>						
	Table 1 "Quick reference data": added						
	Section 8 "Test information": added						
	• Figure 8: superseded by minimized package outline drawing						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	Section 13	"Legal information": update	d				
BAS28_2	19960910	Product specification	-	BAS28_1			
BAS28_1	19960403	Product specification	-	-			

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### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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